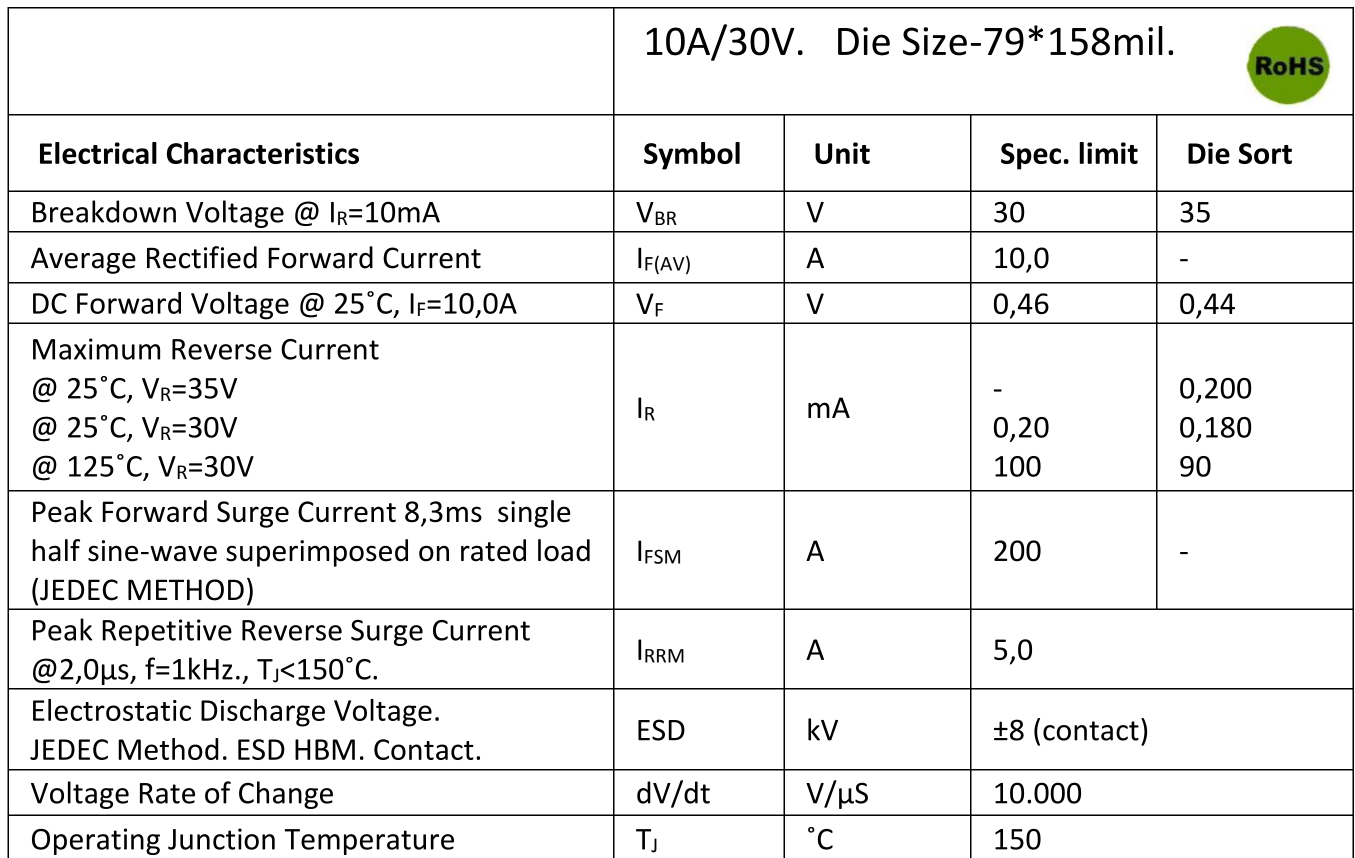
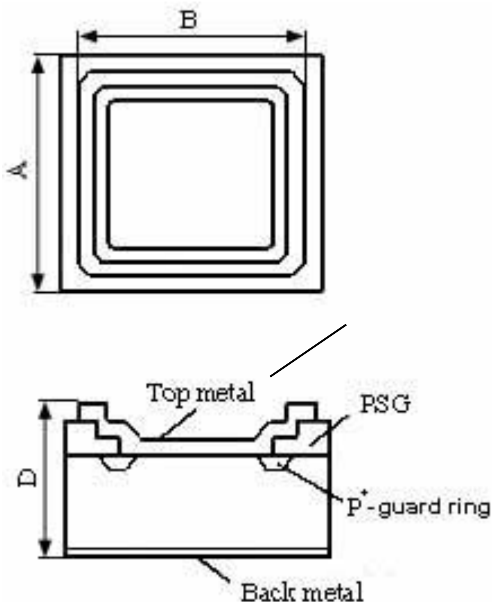


| | 10A/30V. Die Size-79*158mil. RoHS | | | |
|---|---|---|---|---|
| **Electrical Characteristics** | **Symbol** | **Unit** | **Spec. limit** | **Die Sort** |
| Breakdown Voltage @ $I_R$=10mA | $V_{BR}$ | V | 30 | 35 |
| Average Rectified Forward Current | $I_{F(AV)}$ | A | 10,0 | - |
| DC Forward Voltage @ 25˚C, $I_F$=10,0A | $V_F$ | V | 0,46 | 0,44 |
| Maximum Reverse Current<br>@ 25˚C, $V_R$=35V<br>@ 25˚C, $V_R$=30V<br>@ 125˚C, $V_R$=30V | $I_R$ | mA | -<br>0,20<br>100 | 0,200<br>0,180<br>90 |
| Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD) | $I_{FSM}$ | A | 200 | - |
| Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., $T_J$<150˚C. | $I_{RRM}$ | A | 5,0 | |
| Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact. | ESD | kV | ±8 (contact) | |
| Voltage Rate of Change | dV/dt | V/µS | 10.000 | |
| Operating Junction Temperature | $T_J$ | ˚C | 150 | |




| DIM | ITEM | µm |
|---|---|---|
| $A_X$<br>$A_y$ | Wafer Form Die Size | 2000<br>4000 |
| $B_X$<br>$B_y$ | Top Metal Size | 1860<br>3860 |
| D | Thickness | 300max. |
| Scribe line Width | | 80 |

*Top metal*:
a) **Al** – for Wire Bonding;
b) **Al-Ni-Ag** – for Soldering.
Backside metal: **Ti-Ni-Ag**.